



Product Summary

- $V_{DS} = -20V, I_D = -6A$
  - $R_{DS(ON)} < 28m\Omega(max) @ V_{GS} = -2.5V$
  - $R_{DS(ON)} < 20m\Omega(max) @ V_{GS} = -4.5V$
- Reference: SI2333CDS-T1-E3, SI2333CDS-T1-GE3

Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

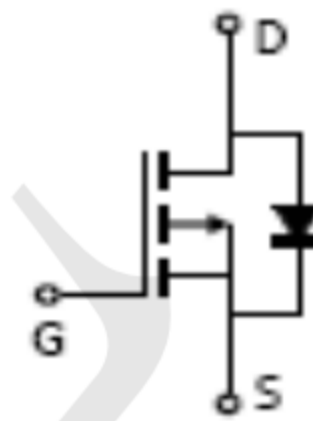
Package and Pin Configuration

SOT-23



Marking: 20P7C

Circuit diagram



Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| Parameter  | Symbol         | Limit      | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage                             | $V_{DS}$       | -20        | V    |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 12$   | V    |
| Drain Current -Continuous                        | $I_D$          | -6         | A    |
| Drain Current -Pulsed (Note 1)                   | $I_{DM}$       | -24        | A    |
| Maximum Power Dissipation                        | $P_D$          | 1.8        | W    |
| Operating Junction and Storage Temperature Range | $T_J, T_{STG}$ | -55 To 150 | °C   |

Thermal Characteristic

|  |                 |    |      |
|--|-----------------|----|------|
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 69 | °C/W |
|--|-----------------|----|------|



**Electrical Characteristics (TA=25°C unless otherwise noted)**

| Parameter                                 | Symbol       | Condition   | Min  | Typ   | Max       | Unit       |
|---|--------------|---|------|-------|-----------|------------|
| <b>Off Characteristics</b>                |              |   |      |       |           |            |
| Drain-Source Breakdown Voltage            | $BV_{DSS}$   | $V_{GS}=0V, I_D=-250\mu A$  | -20  | -     | -         | V          |
| Zero Gate Voltage Drain Current           | $I_{DSS}$    | $V_{DS}=-12V, V_{GS}=0V$  | -    | -     | -1        | $\mu A$    |
| Gate-Body Leakage Current                 | $I_{GSS}$    | $V_{GS}=\pm 12V, V_{DS}=0V$   | -    | -     | $\pm 100$ | nA         |
| <b>On Characteristics (Note 3)</b>        |              |   |      |       |           |            |
| Gate Threshold Voltage                    | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=-250\mu A$                                      | -0.4 | -0.55 | -1.0      | V          |
| Drain-Source On-State Resistance          | $R_{DS(ON)}$ | $V_{GS}=-4.5V, I_D=-6A$   | -    | 18    | 20        | m $\Omega$ |
|   |              | $V_{GS}=-2.5V, I_D=-5A$   | -    | 22    | 28        |            |
| Forward Transconductance                  | $g_{FS}$     | $V_{DS}=-5V, I_D=-6A$   |      | 20    | -         | S          |
| <b>Dynamic Characteristics (Note 4)</b>   |              |   |      |       |           |            |
| Input Capacitance                         | $C_{iss}$    | $V_{DS}=-6V, V_{GS}=0V,$<br>$F=1.0MHz$                              | -    | 1730  | -         | PF         |
| Output Capacitance                        | $C_{oss}$    |   | -    | 320   | -         | PF         |
| Reverse Transfer Capacitance              | $C_{rss}$    |   | -    | 210   | -         | PF         |
| <b>Switching Characteristics (Note 4)</b> |              |   |      |       |           |            |
| Turn-on Delay Time                        | $t_{d(on)}$  | $V_{DD}=-6V, I_D=-1A,$<br>$R_L=6\Omega, V_{GEN}=-4.5V, R_g=6\Omega$ | -    | 20    | -         | nS         |
| Turn-on Rise Time                         | $t_r$        |   | -    | 35    | -         | nS         |
| Turn-Off Delay Time                       | $t_{d(off)}$ |   | -    | 90    | -         | nS         |
| Turn-Off Fall Time                        | $t_f$        |   | -    | 70    | -         | nS         |
| Total Gate Charge                         | $Q_g$        | $V_{DS}=-6V, I_D=-6A, V_{GS}=-4.5V$                                 | -    | 19.5  | -         | nC         |
| Gate-Source Charge                        | $Q_{gs}$     |   | -    | 4.1   | -         | nC         |
| Gate-Drain Charge                         | $Q_{gd}$     |   | -    | 5.2   | -         | nC         |
| <b>Drain-Source Diode Characteristics</b> |              |   |      |       |           |            |
| Diode Forward Voltage (Note 3)            | $V_{SD}$     | $V_{GS}=0V, I_S=-1.0A$  | -    | -     | -1.2      | V          |
| Diode Forward Current (Note 2)            | $I_S$        |   | -    | -     | -6        | A          |





Typical Electrical and Thermal Characteristics

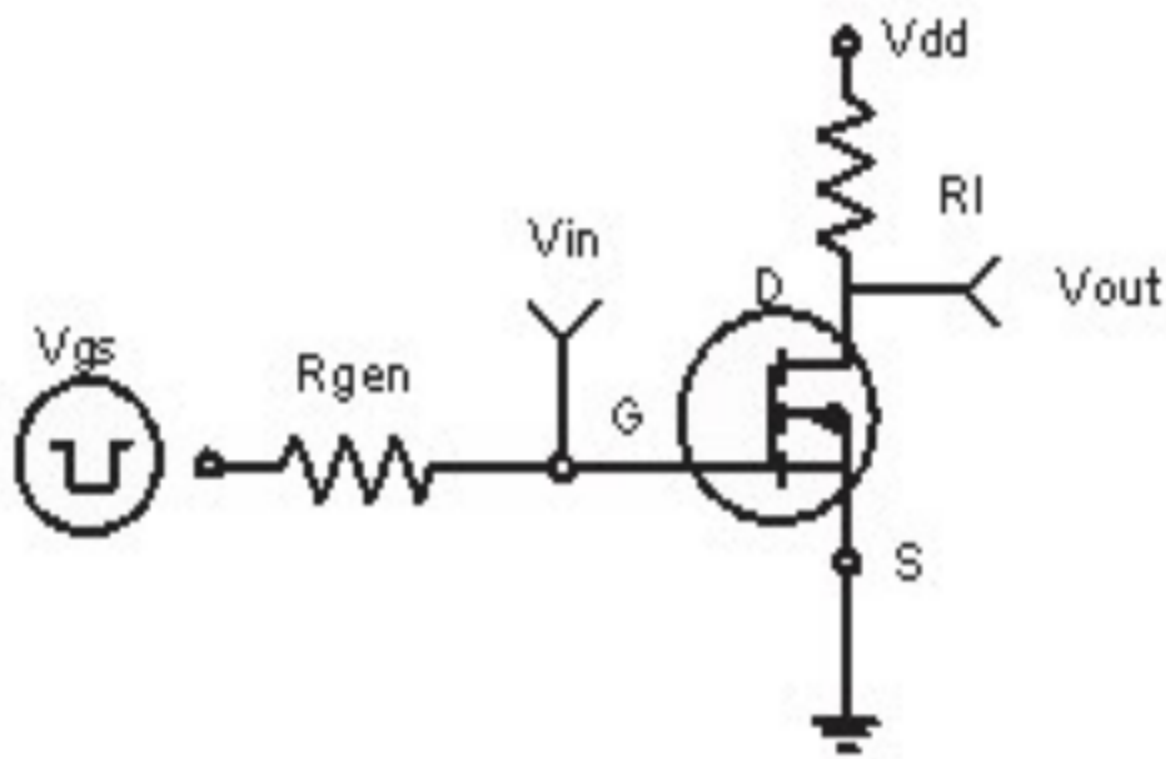


Figure 1: Switching Test Circuit

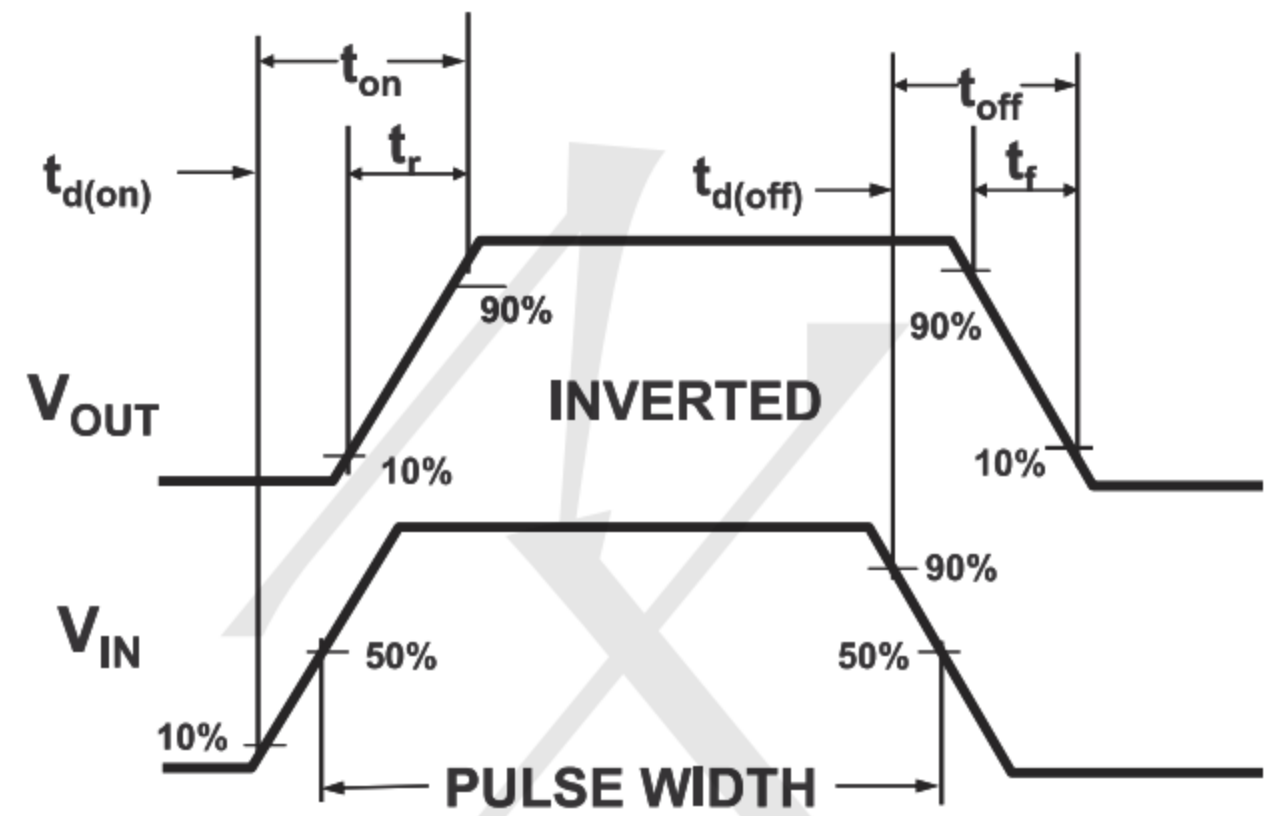
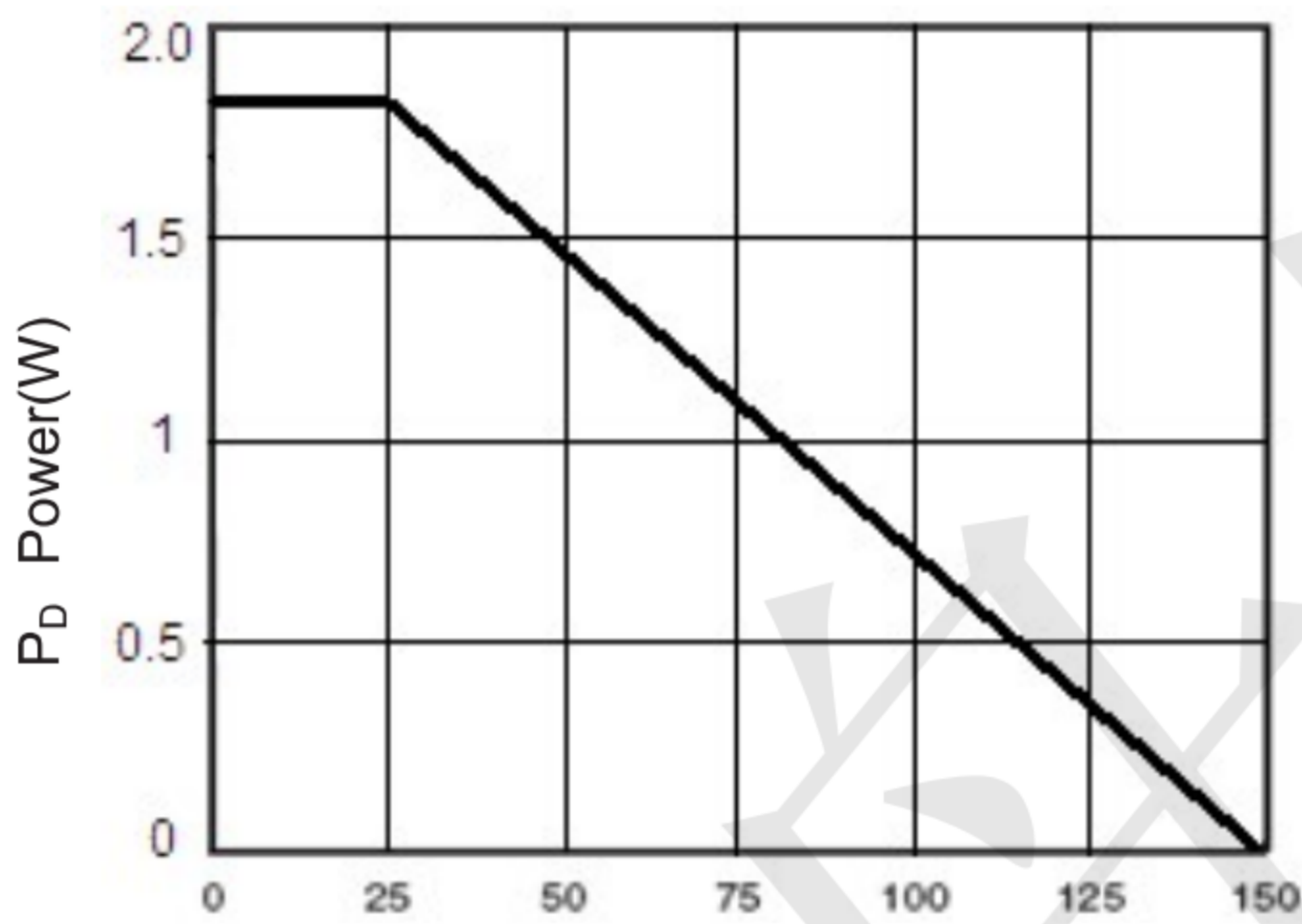
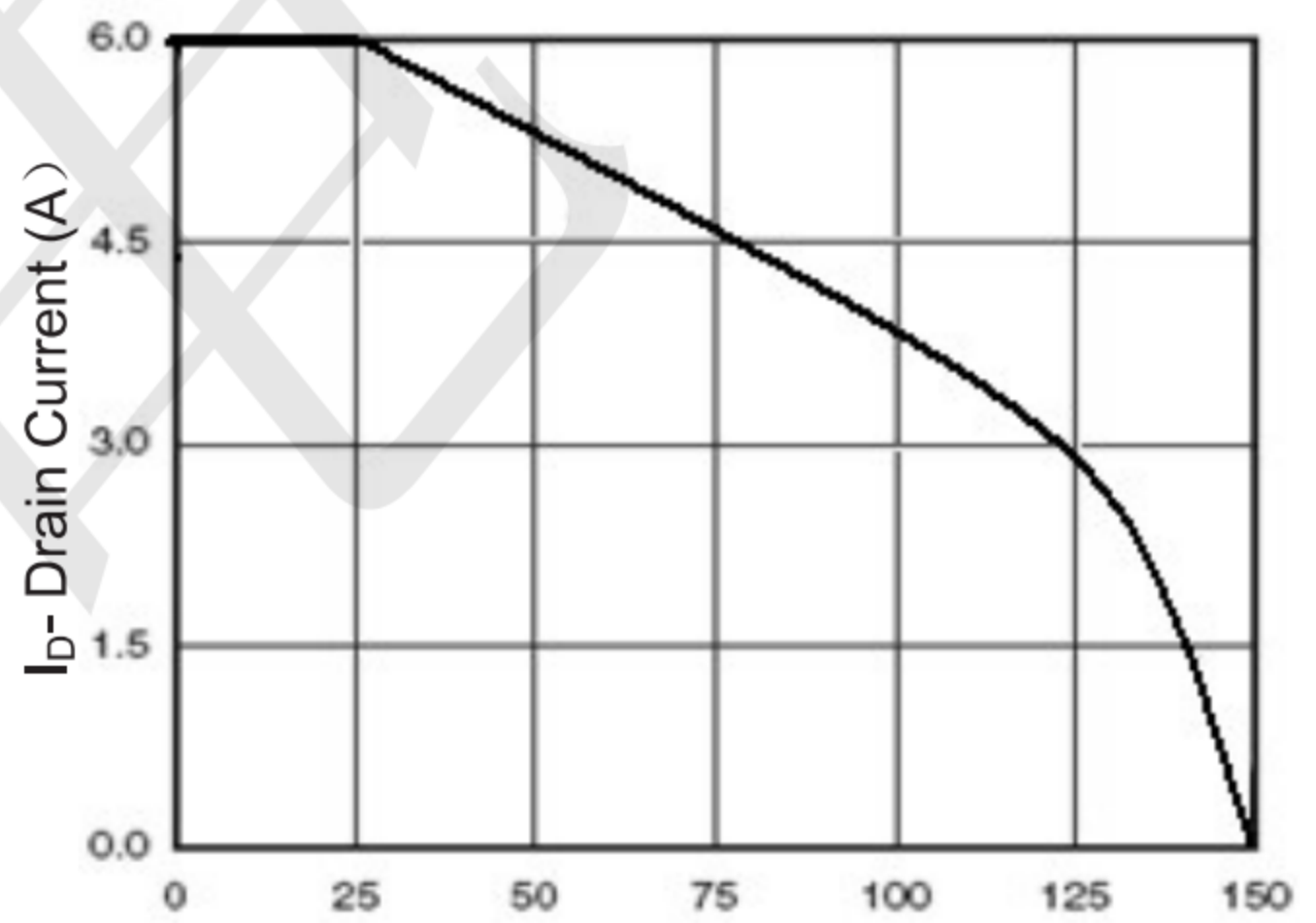


Figure 2: Switching Waveforms



T<sub>J</sub>-Junction Temperature(°C)

Figure 3 Power Dissipation



T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Drain Current

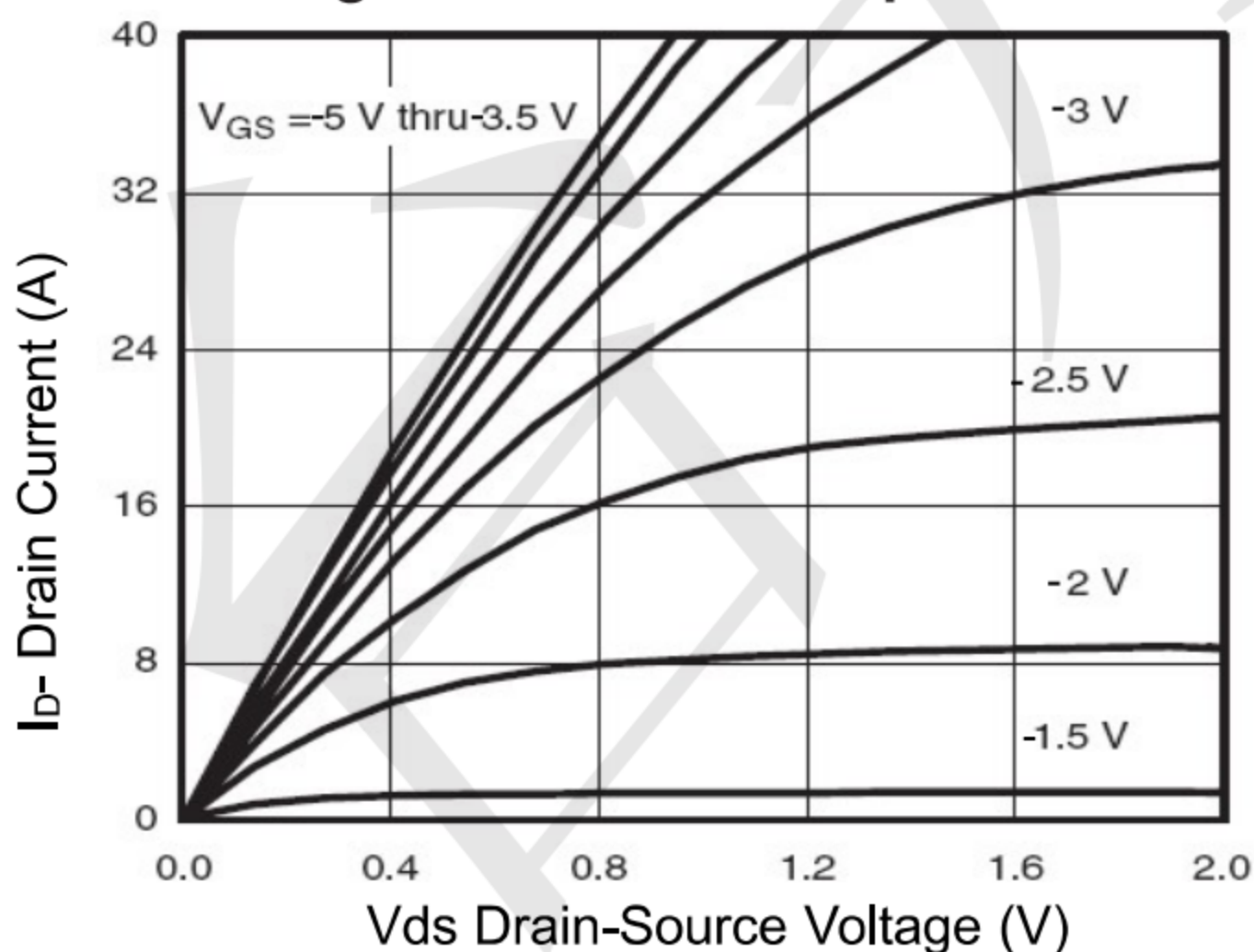


Figure 5 Output Characteristics

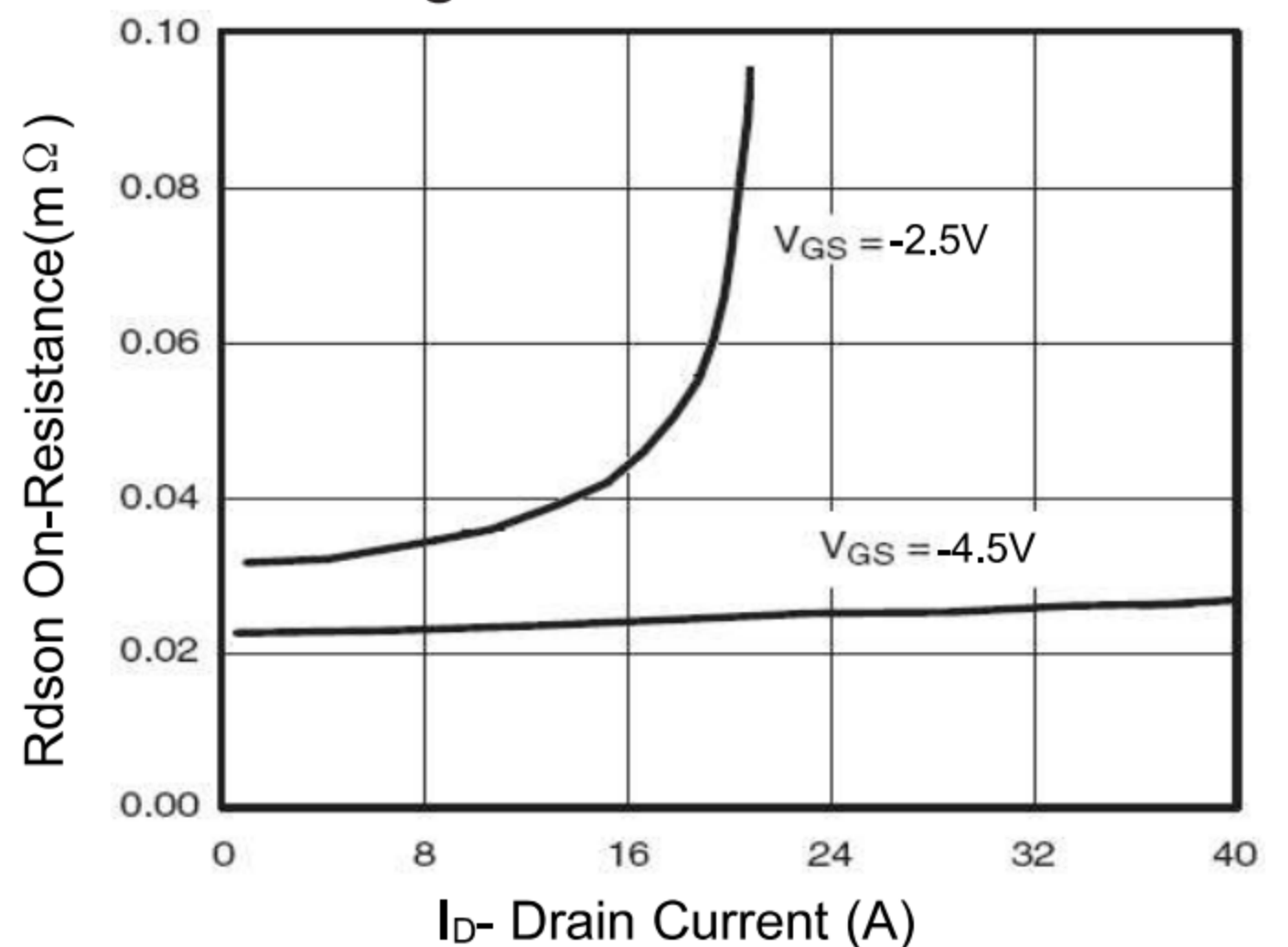


Figure 6 Drain-Source On-Resistance

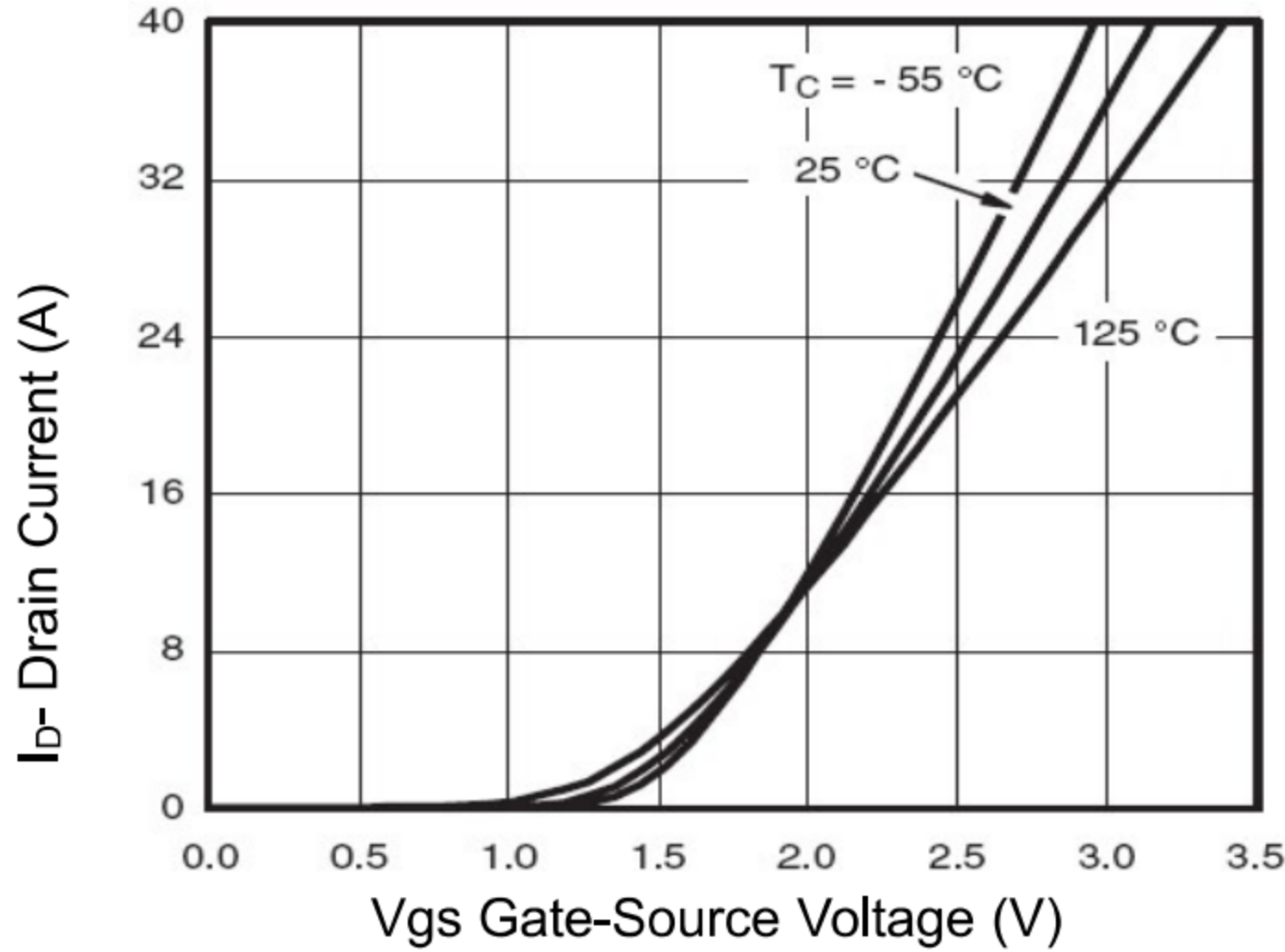


Figure 7 Transfer Characteristics

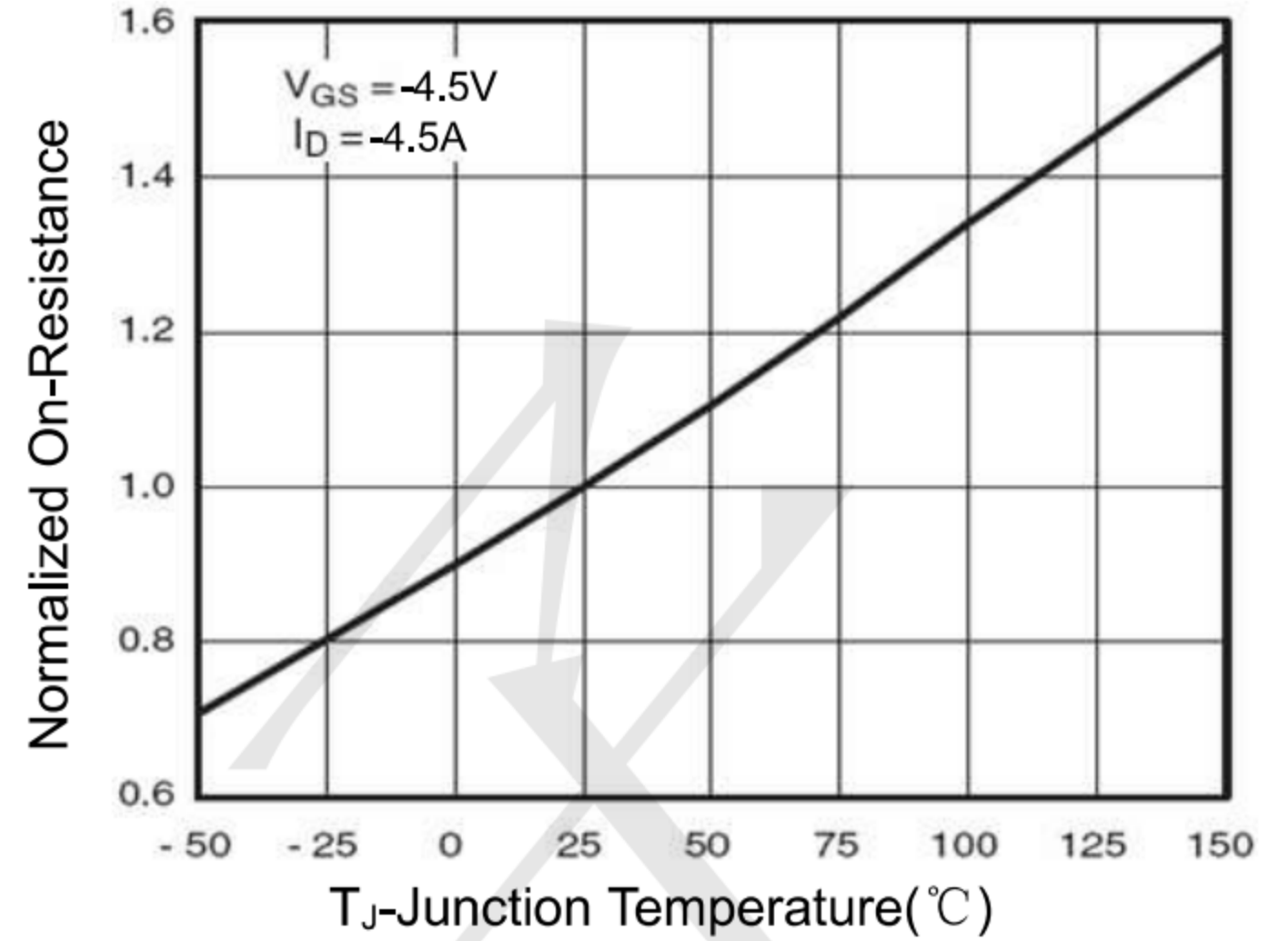


Figure 8 Drain-Source On-Resistance

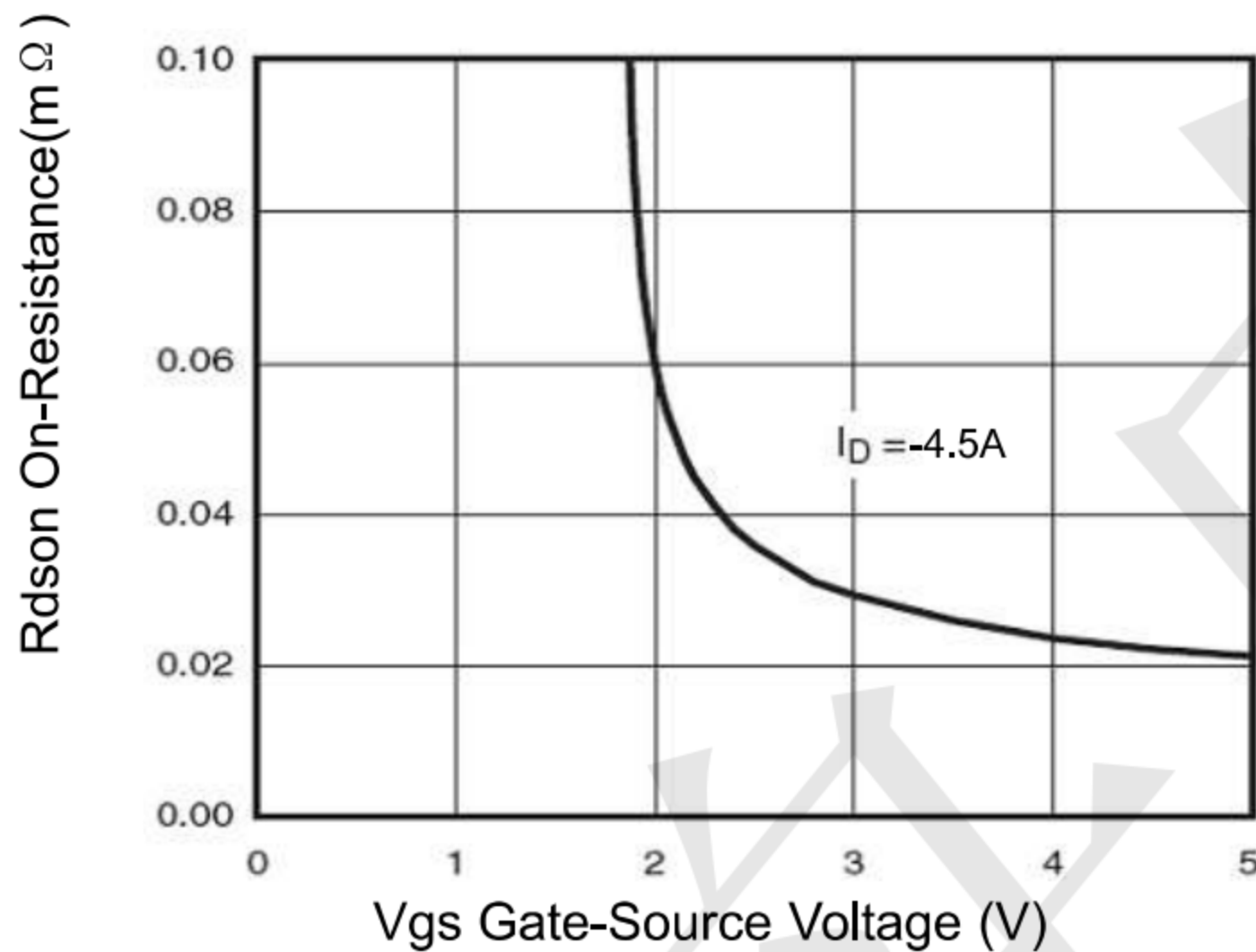


Figure 9 Rdson vs Vgs

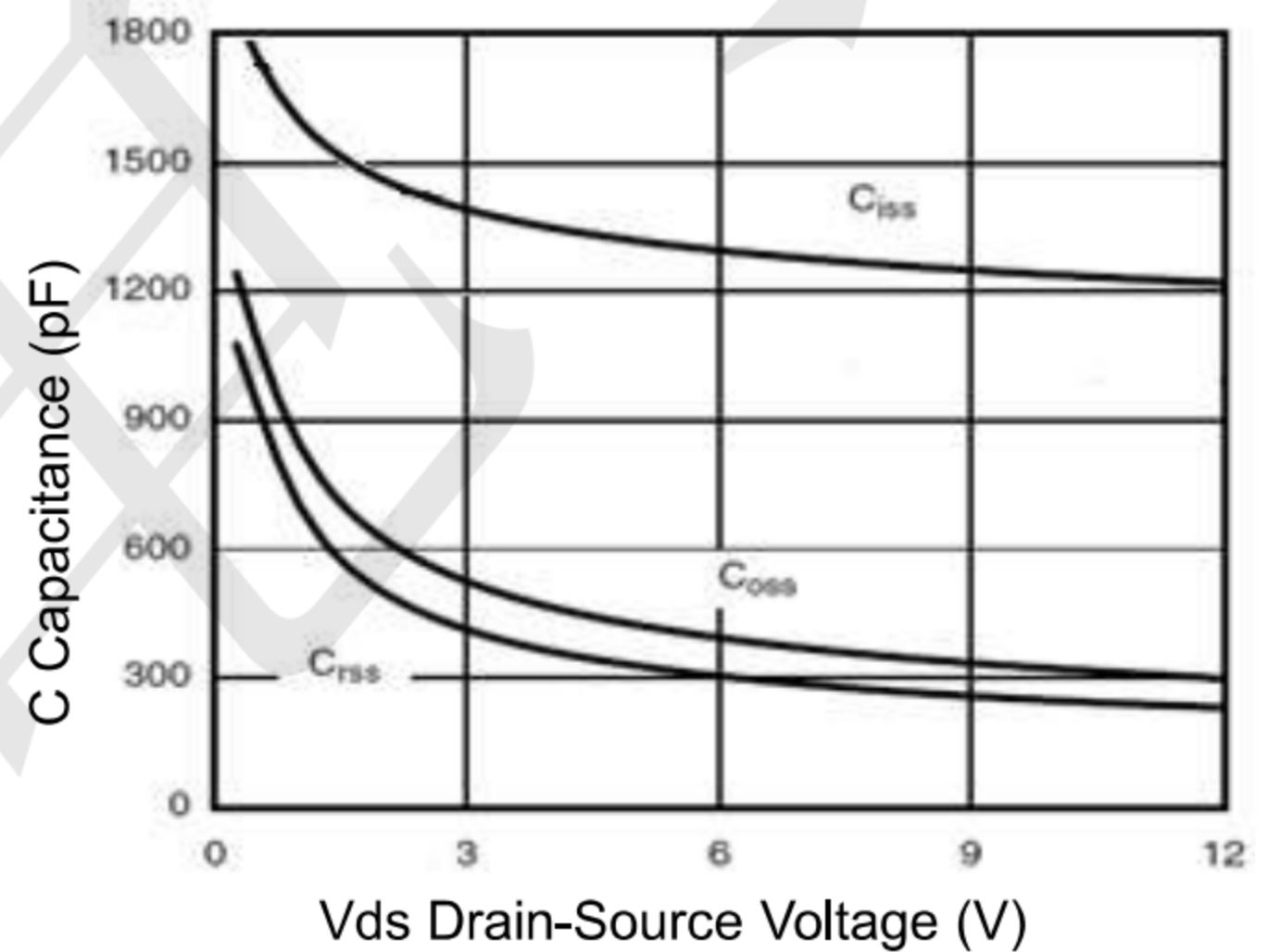


Figure 10 Capacitance vs Vds

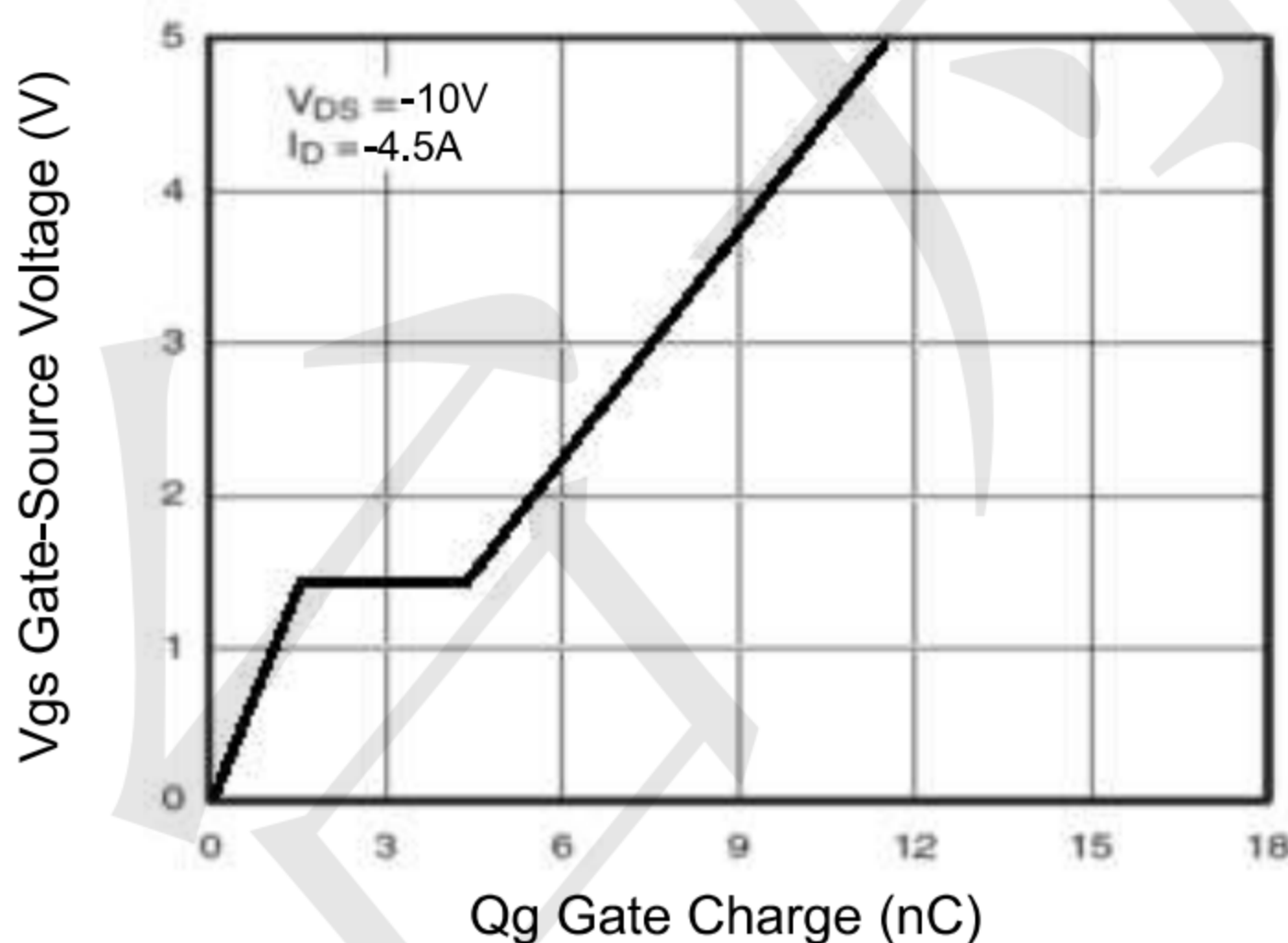


Figure 11 Gate Charge

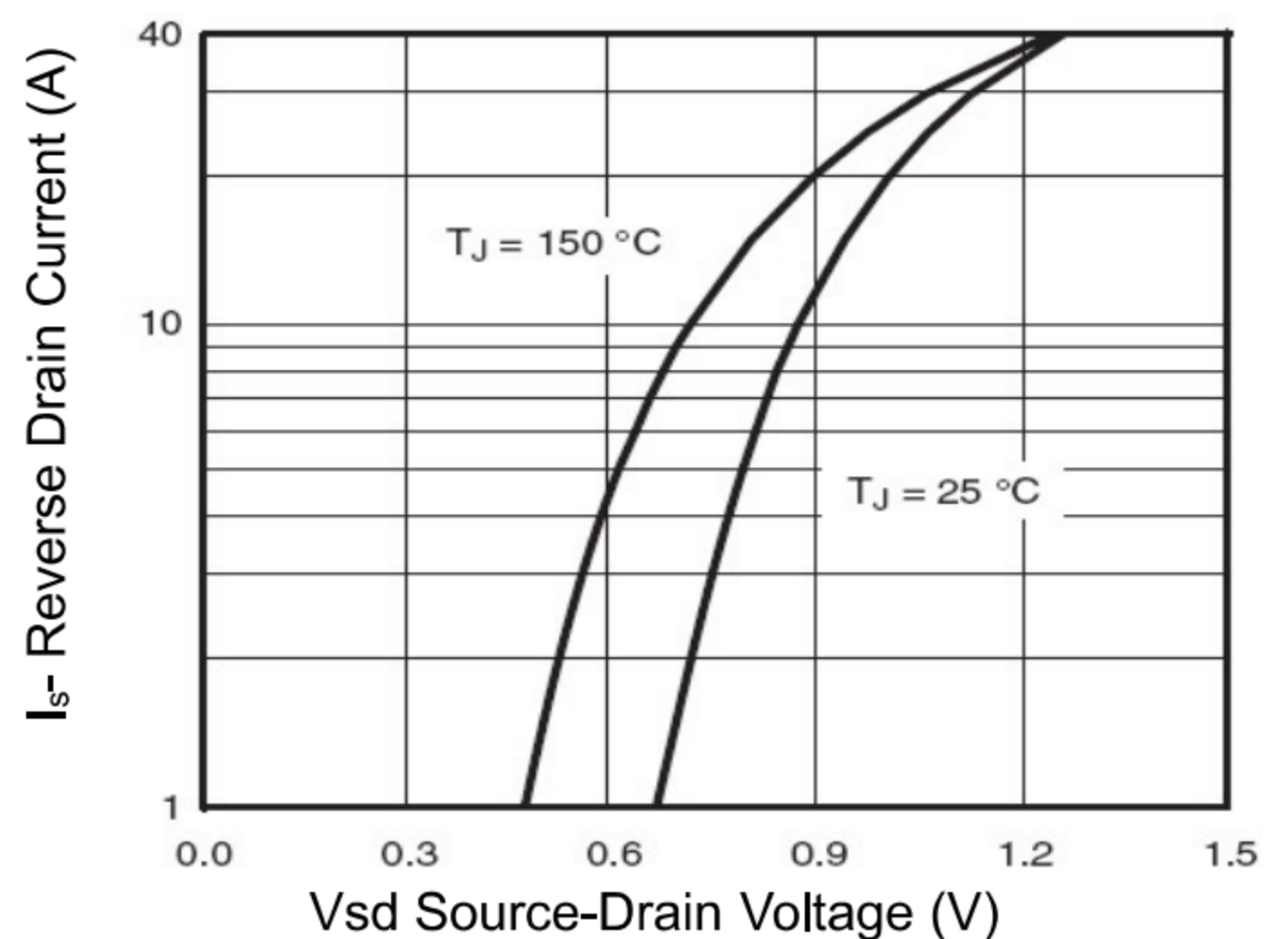


Figure 12 Source- Drain Diode Forward





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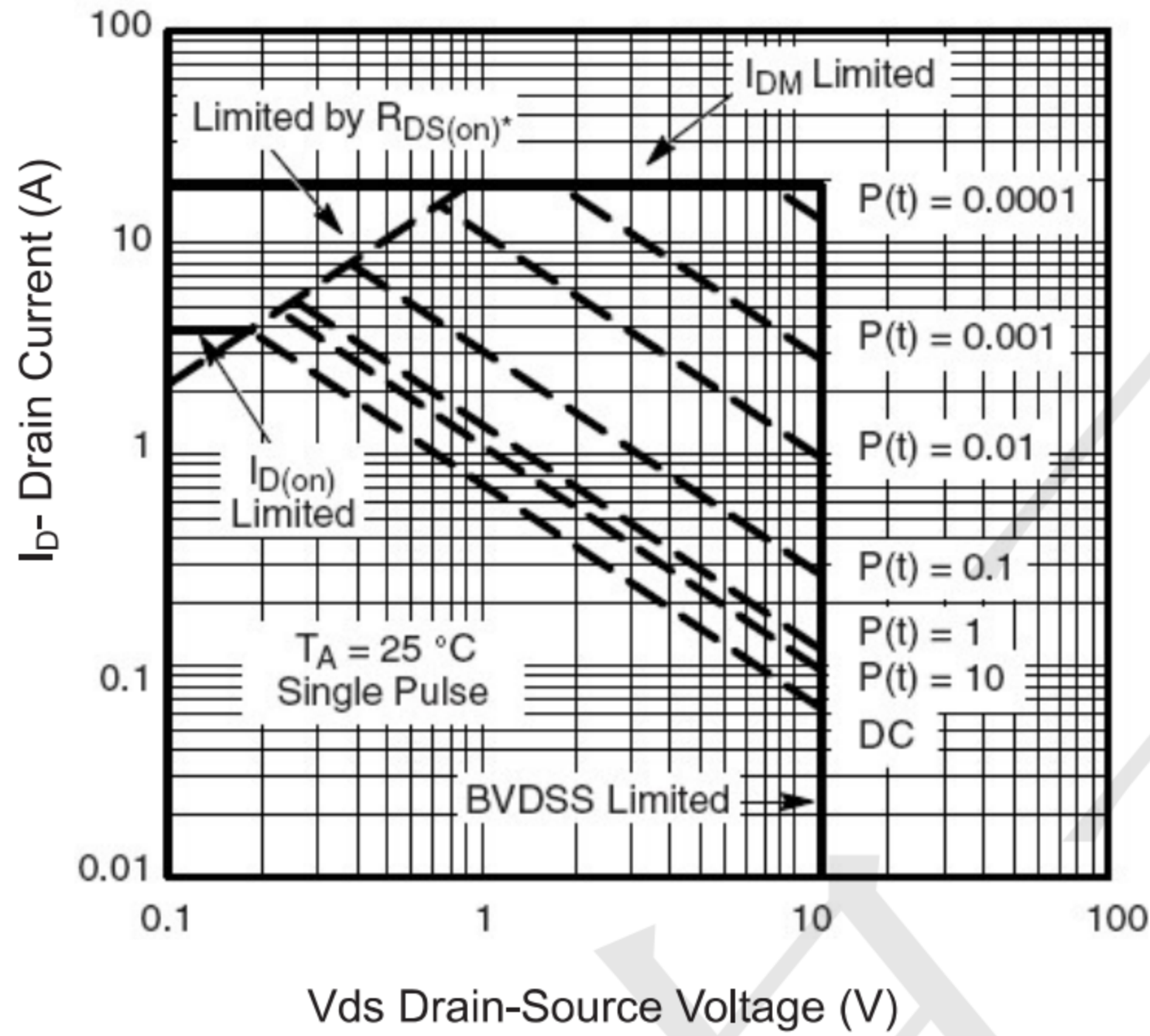


Figure 13 Safe Operation Area

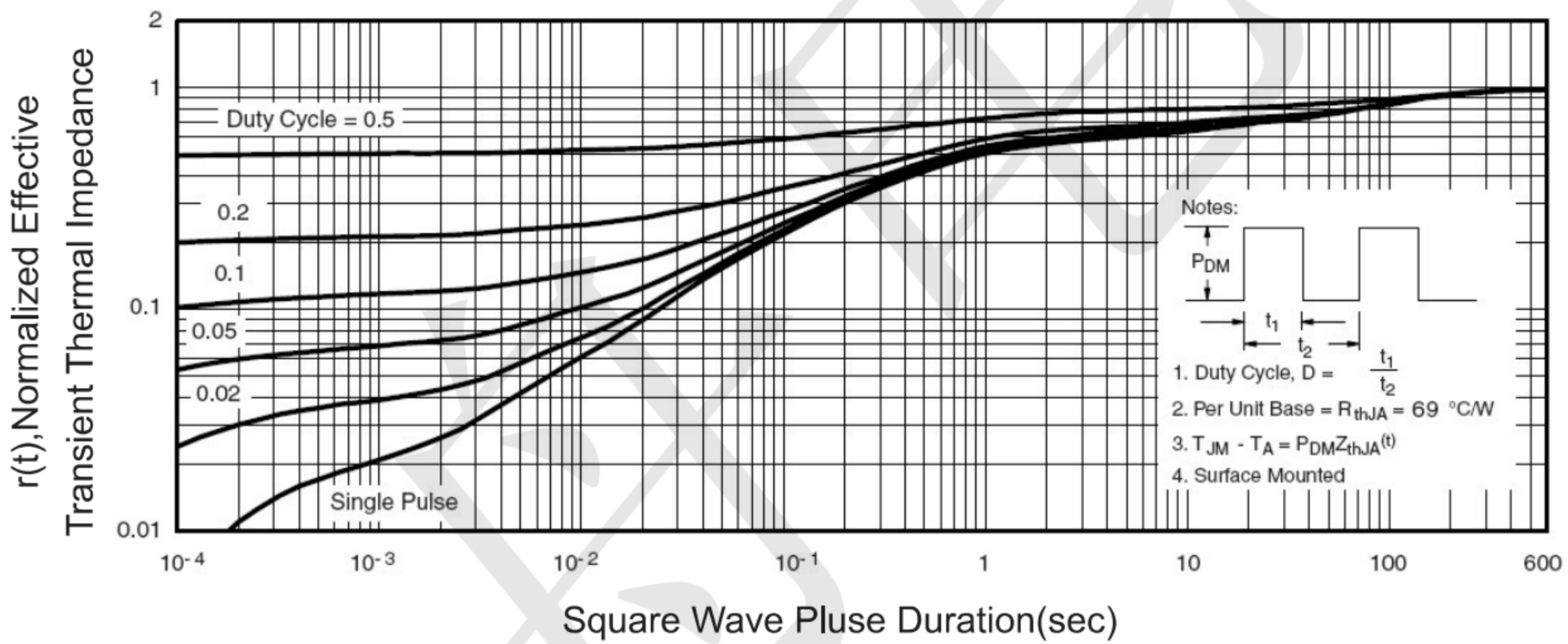
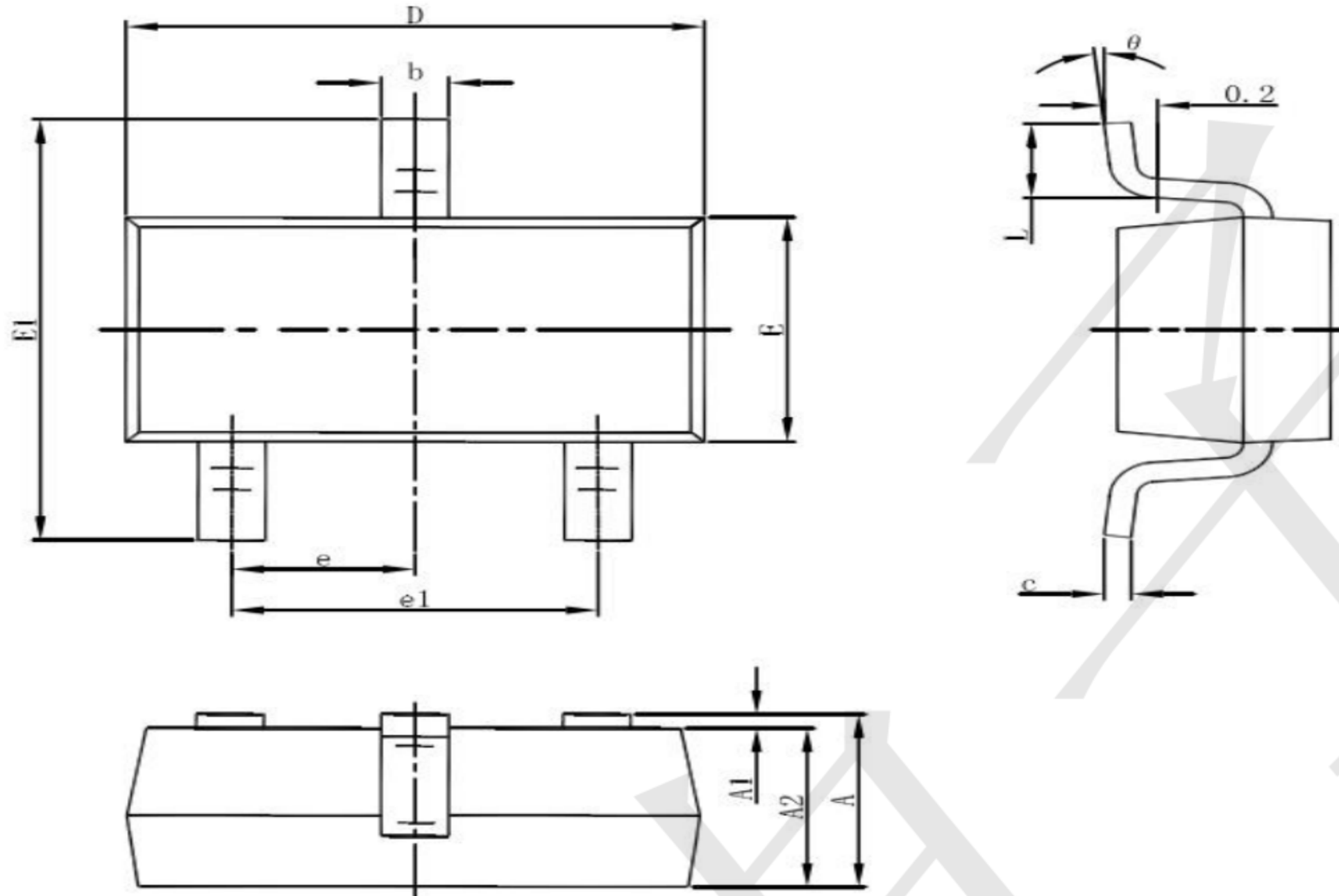


Figure 14 Normalized Maximum Transient Thermal Impedance

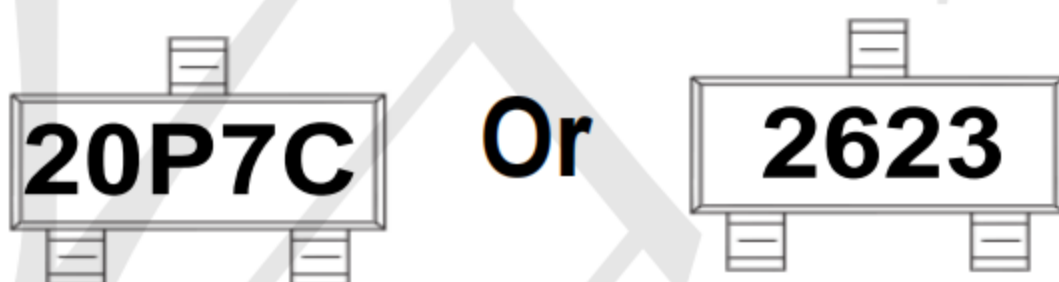


3-pin SOT23-3 Outline Dimensions



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 1.050                     | 1.250 | 0.041                | 0.049 |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2     | 1.050                     | 1.150 | 0.041                | 0.045 |
| b      | 0.300                     | 0.500 | 0.012                | 0.020 |
| c      | 0.100                     | 0.200 | 0.004                | 0.008 |
| D      | 2.820                     | 3.020 | 0.111                | 0.119 |
| E      | 1.500                     | 1.700 | 0.059                | 0.067 |
| E1     | 2.650                     | 2.950 | 0.104                | 0.116 |
| e      | 0.950(BSC)                |       | 0.037(BSC)           |       |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079 |
| L      | 0.300                     | 0.600 | 0.012                | 0.024 |
| theta  | 0°                        | 8°    | 0°                   | 8°    |

Marking:



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